

# High-Performance 512 x 8 Registered PROM

# 53 / 63RA481 53 / 63RA481A

## Features/Benefits

- Versatile synchronous and asynchronous enables
- Asynchronous preset and clear
- Edge-triggered "D" registers
- 8-bit-wide in 24-pin SKINNYDIP® for high board density
- On-chip register simplifies system timing
- Faster cycle times
- 16 mA  $I_{OL}$  output drive capability
- Reliable titanium-tungsten fuses (Ti-W), with programming yields typically greater than 98%.

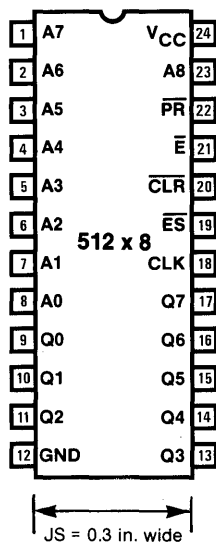
## Applications

- Microprogram control store
- State sequencers/state machines
- Next address generation
- Mapping PROM

## Description

The 53/63RA481 and 53/63RA481A are 512 x 8 Registered PROMs with on-chip "D" type registers, versatile output enable control through synchronous and asynchronous three-state enable inputs, and asynchronous preset and clear.

## Pin Configuration



## Ordering Information

MEMORY		PACKAGE		DEVICE TYPE	
SIZE	PERF.	PINS	TYPE	MIL	COM
4 K	Standard	24 (28)	NS,	53RA481	63RA481
	Enhanced		JS (L)	53RA481A	63RA481A

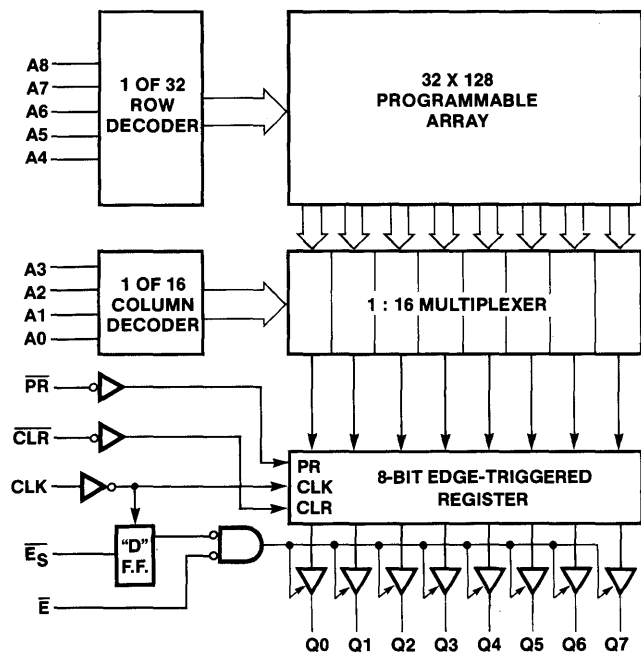
Flatpak — Contact the factory.

Data is transferred into the output registers on the rising edge of the clock. The data will appear at the outputs provided that both the asynchronous  $\bar{E}$  and synchronous  $\bar{ES}$  enables are Low. Prior to the positive clock edge, register data are not affected by changes in addressing or synchronous enable inputs.

Memory expansion and data control is made more flexible with synchronous and asynchronous enable inputs. Outputs may be set to the high-impedance state at any time by setting  $\bar{E}$  to a High or if  $\bar{ES}$  is High when the rising clock edge occurs. When  $V_{CC}$  power is first applied, the synchronous enable flip-flop will be in the set condition causing the outputs to be in the high-impedance state.

The output registers will be set to all Highs when preset is Low independent of the state of clock. The output registers will be reset to all Lows when clear is Low independent of the state of clock. Note that preset and clear are exclusive operations and cannot occur simultaneously.

## Block Diagram



SKINNYDIP® is a registered trademark of Monolithic Memories

2175 Mission College Boulevard, Santa Clara, CA 95050 Tel: (408) 970-9700

TWX: 910-338-2376  
TWX: 910-338-2374

**Monolithic  
Memories**

**Absolute Maximum Ratings**

	<b>Operating</b>	<b>Programming</b>
Supply voltage $V_{CC}$ .....	-0.5 V to 7 V	12 V
Input voltage .....	-1.5 V to 7 V	7 V
Off-state output voltage .....	-0.5 V to 5.5 V	12 V
Storage temperature .....	-65° to +150° C	

**Operating Conditions**

SYMBOL	PARAMETER	TYP†	COMMERCIAL				MILITARY				UNIT
			63RA481A		63RA481		53RA481A		53RA481		
			MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
$V_{CC}$	Supply voltage	5.0	4.75	5.25	4.75	5.25	4.5	5.5	4.5	5.5	V
$T_A$	Operating free-air temperature	25	0	75	0	75	-55	125	-55	125	°C
$t_w$	Width of clock (High or Low)	10	20		20		20		20		ns
$t_{prw}$	Width of preset or clear (Low) to Output (High or Low)	10	20		20		20		20		ns
$t_{clr}$											
$t_{pr}$	Recovery from preset or clear (Low) to clock High	11	20		20		25		25		ns
$t_{clr}$											
$t_s (A)$	Setup time from address to clock	22	30		35		35		45		ns
$t_s (\overline{ES})$	Setup time from $\overline{ES}$ to clock	7	10		10		15		15		ns
$t_h (A)$	Hold time from address to clock	-5	0		0		0		0		ns
$t_h (\overline{ES})$	Hold time from $\overline{ES}$ to clock	-3	5		5		5		5		ns

**Electrical Characteristics Over Operating Conditions**

SYMBOL	PARAMETER	TEST CONDITIONS		MIN	TYP†	MAX	UNIT
$V_{IL}$	Low-level input voltage					0.8	V
$V_{IH}$	High-level input voltage			2.0			V
$V_{IC}$	Input clamp voltage	$V_{CC} = \text{MIN}$	$I_I = -18 \text{ mA}$			-1.2	V
$I_{IL}$	Low-level input current	$V_{CC} = \text{MAX}$	$V_I = 0.4 \text{ V}$			-0.25	mA
$I_{IH}$	High-level input current	$V_{CC} = \text{MAX}$	$V_I = V_{CC}$			40	$\mu\text{A}$
$V_{OL}$	Low-level output voltage	$V_{CC} = \text{MIN}$	$I_{OL} = 16 \text{ mA}$			0.5	V
$V_{OH}$	High-level output voltage	$V_{CC} = \text{MIN}$	MIL $I_{OH} = -2 \text{ mA}$ COM $I_{OH} = -3.2 \text{ mA}$	2.4			V
$I_{OZL}$	Off-state output current	$V_{CC} = \text{MAX}$	$V_O = 0.4 \text{ V}$			-40	$\mu\text{A}$
$I_{OZH}$			$V_O = 2.4 \text{ V}$			40	
$I_{OS}$	Output short-circuit current*	$V_{CC} = 5 \text{ V}$	$V_O = 0 \text{ V}$	-20		-90	mA
$I_{CC}$	Supply Current	$V_{CC} = \text{MAX}$	All outputs open.		130	180	mA

\* Not more than one output should be shorted at a time and duration of the short-circuit should not exceed one second.

† Typical at 5.0 V  $V_{CC}$  and 25° C  $T_A$ .

**Switching Characteristics** Over Operating Conditions and using Standard Test Load

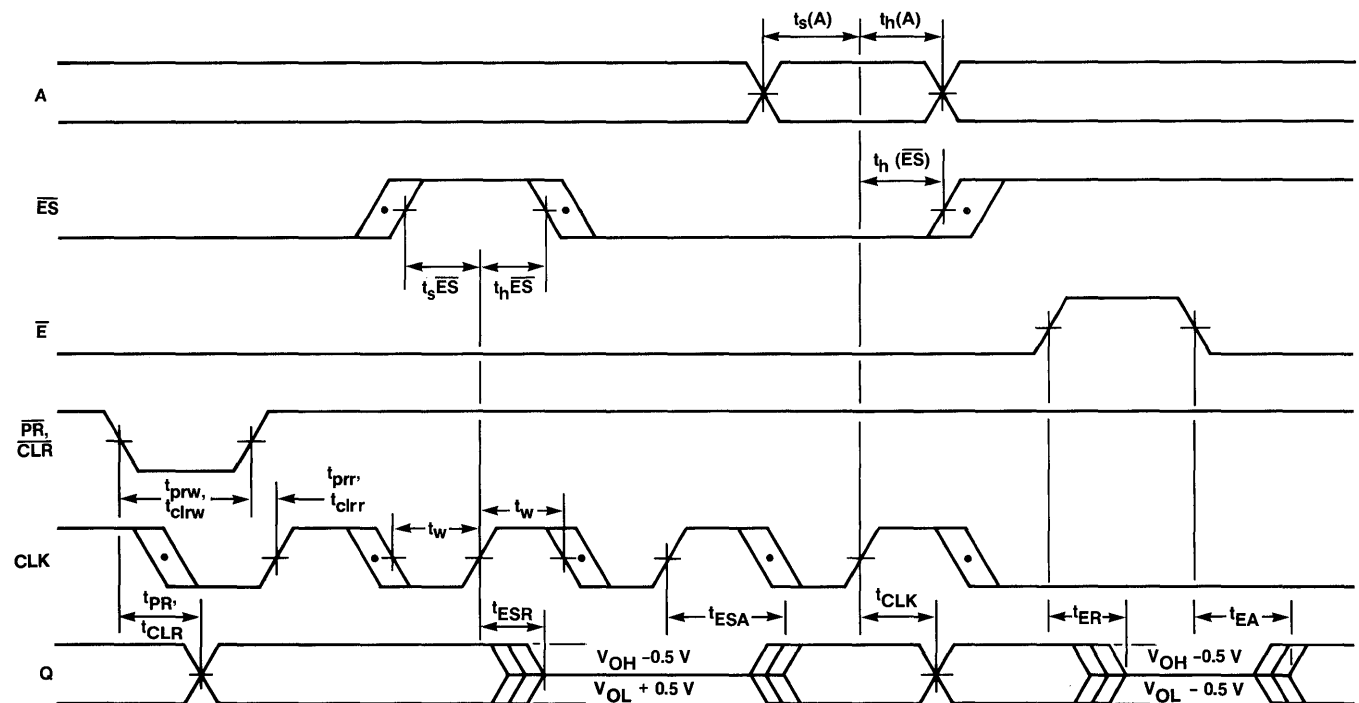
SYMBOL	PARAMETER	TYP†	COMMERCIAL		MILITARY		UNIT
			63RA481A	63RA481	53RA481A	53RA481	
			MIN	MAX	MIN	MAX	
$t_{CLK}$	Clock to output Delay	11	15	20	20	25	ns
$t_{ESA}$	Clock to output access time ( $\overline{ES}$ )	14	25	30	30	35	ns
$t_{ESR}$	Clock to output recovery time ( $\overline{ES}$ )	14	25	30	30	35	ns
$t_{EA}$	Enable to output access time ( $\overline{E}$ )	10	20	30	25	35	ns
$t_{ER}$	Disable to output recovery time ( $\overline{E}$ )	10	20	30	25	35	ns
$t_{PR}$	Preset to output delay ( $\overline{PR}$ )	15	20	25	25	30	ns
$t_{CLR}$	Clear to output delay ( $\overline{CLR}$ )	18	25	30	35	40	ns

† Typical at 5.0 V  $V_{CC}$  and 25 °C  $T_A$

**Function Table**

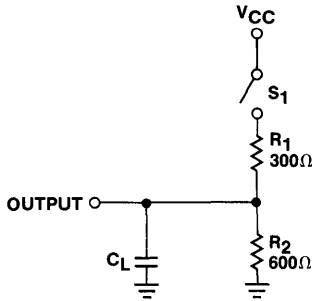
$\overline{E}$	$\overline{ES}$	CLK	$\overline{PR}$	$\overline{CLR}$	A8-A0	Q7-Q0	Operation
H	X	X	X	X	X	Z	High-Impedance
X	H	↑	X	X	X	Z	High-Impedance
L	L	X	L	H	X	H	Preset
L	L	X	H	L	X	L	Clear
L	L	X	L	L	X		Illegal Operation
L	L	↑	H	H	A	Data	Memory Access

**Definition of Waveforms**

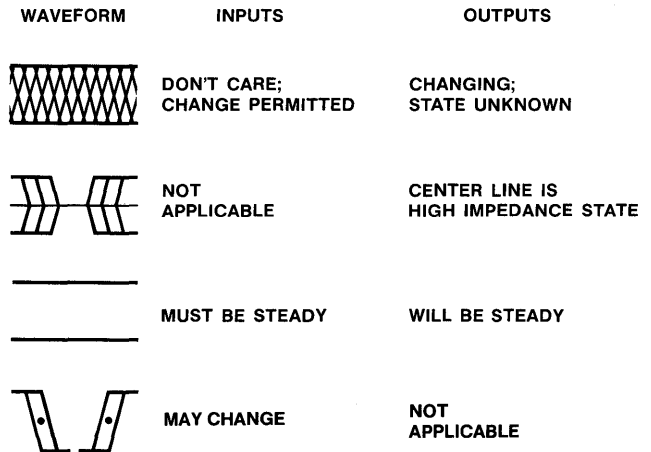


- NOTES: 1. Input pulse amplitude 0 V to 3.0 V.  
 2. Input rise and fall times 2-5 ns from 1.0 V to 2.0 V.  
 3. Input access measured at the 1.5 V level.  
 4. Switch  $S_1$  is closed.  $C_L = 30$  pF and outputs measured at 1.5 V level for all tests except  $t_{ESA}$  and  $t_{ESR}$ .  
 5.  $t_{EA}$  and  $t_{ESA}$  are measured at the 1.5 V output level with  $C_L = 30$  pF.  $S_1$  is open for high-impedance to "1" test and closed for high impedance to "0" test.  
 $t_{ER}$  and  $t_{ESR}$  are tested with  $C_L = 5$  pF.  $S_1$  is open for "1" to high-impedance test, measured at  $V_{OH} - 0.5 V$  output level;  $S_1$  is closed for "0" to high-impedance test measured at  $V_{OL} + 0.5 V$  output level.

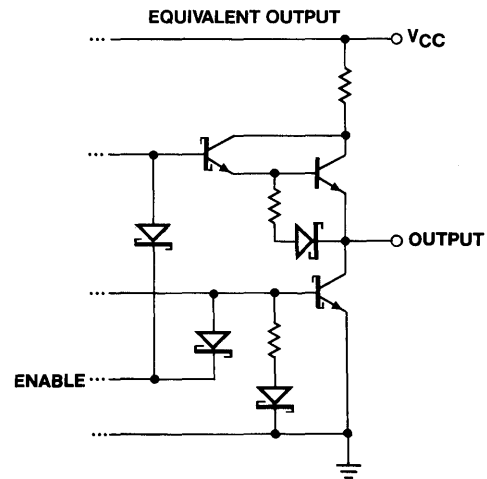
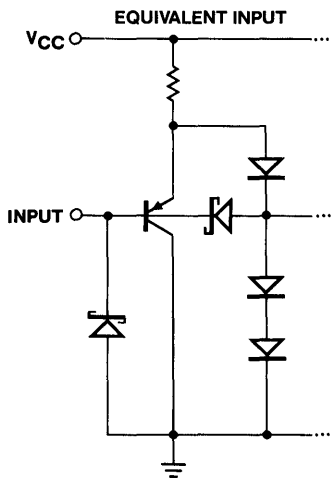
**Switching Test Load**



**Definition of Timing Diagram**



**Schematic of Inputs and Outputs**



**Programming**

The 53/63RA481 and 53/63RA481A are programmed with the same programming algorithm as all other Monolithic Memories' registered PROMs. For details refer to Monolithic Memories' LSI Data Book.

Monolithic Memories' PROMs are designed and tested to give a programming yield greater than 98%. If your programming yield is lower, check your programmer. It may not be properly calibrated.

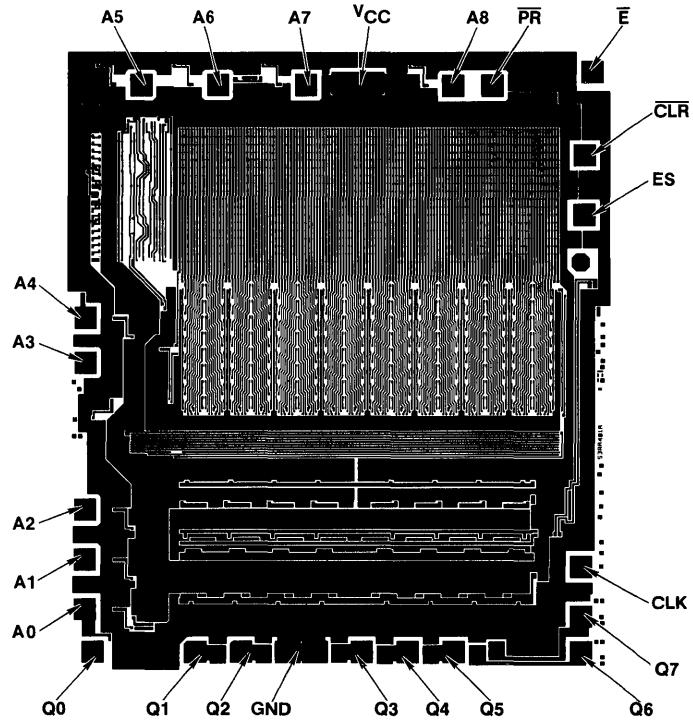
Programming is final manufacturing — it must be quality-controlled. Equipment must be calibrated as regular routine, ideally under the actual conditions of use. Each time a new board or a new programming module is inserted, the whole system should be checked. Both timing and voltage must meet published specifications for the device.

**Remember — The best PROMs available can be made unreliable by improper programming techniques.**

**Commercial Programmers**

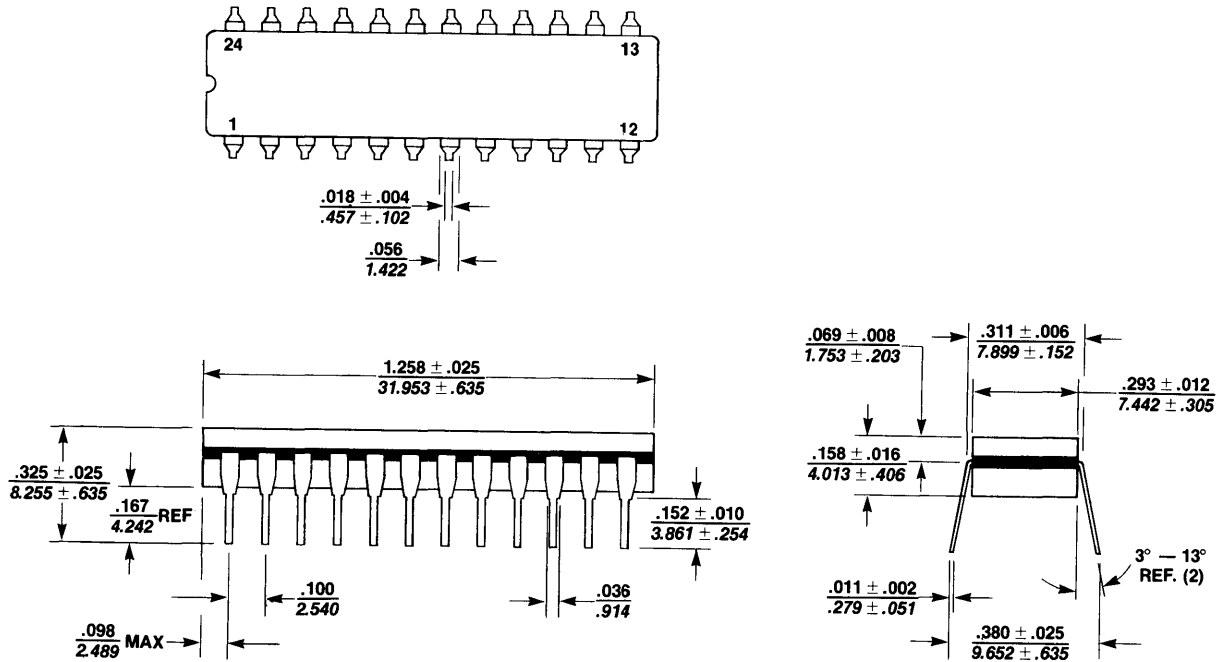
MANUFACTURER	PROGRAMMER TYPE	PROGRAMMING MODULE	SOCKET CONFIGURATION
Data I/O	Unipak Rev-V05 Unipak 2 Rev-V04	Family Code 18	Pinout Code 65

Metal Mask Layout



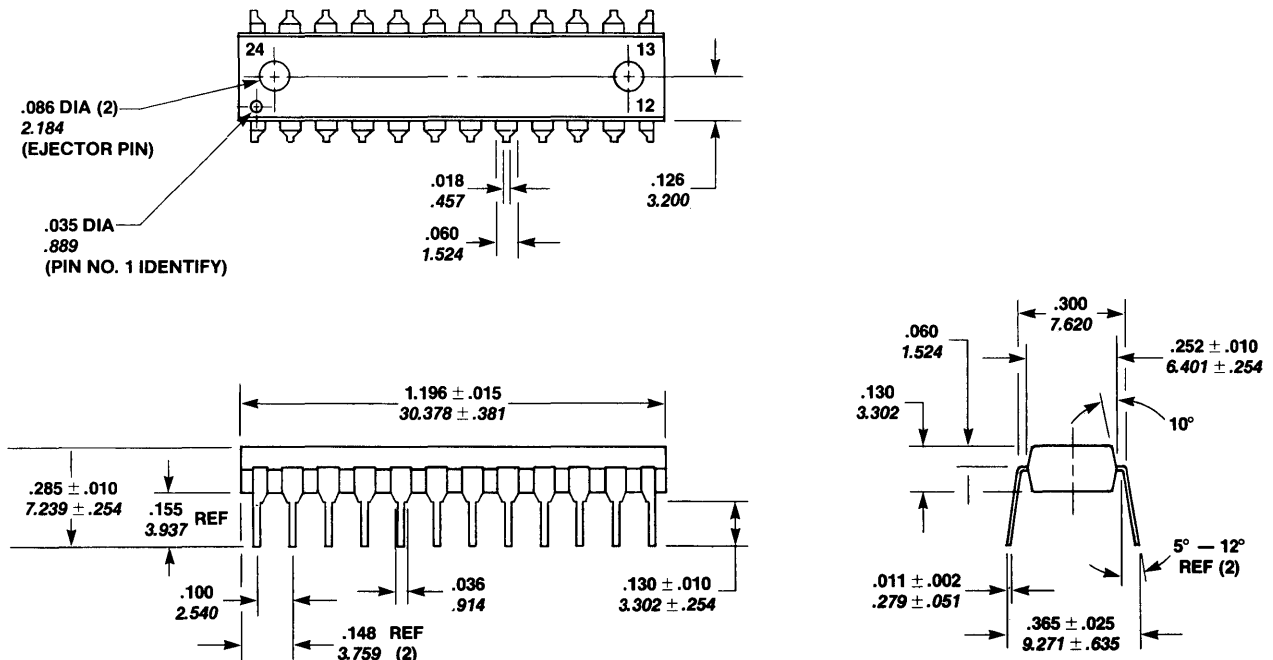
Package Drawings

J24S Ceramic SKINNYDIP



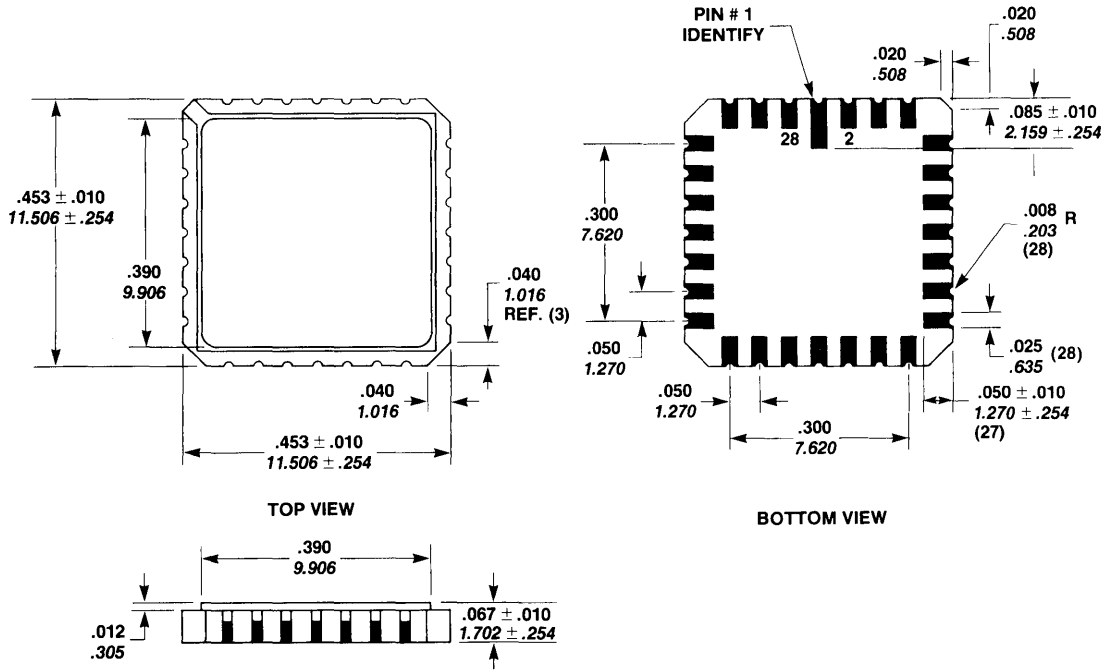
UNLESS OTHERWISE SPECIFIED:  
ALL DIMENSIONS MIN.-MAX. IN INCHES  
ALL DIMENSIONS MIN.-MAX. IN MILLIMETERS

N24S Molded SKINNYDIP



UNLESS OTHERWISE SPECIFIED:  
ALL DIMENSIONS MIN.-MAX. IN INCHES  
ALL DIMENSIONS MIN.-MAX. IN MILLIMETERS

L28 Leadless Chip Carrier



NOTES:

1. Top Dimension Specified in Inches. Bottom Dimension Specified in mm.
2. All Nominal Dimensions Are  $\pm .007$  inches Unless Otherwise Specified.
3. Solder Fillets on Lid Edges Not Shown.

---

# **Monolithic Memories**

## **Americas**

### **Monolithic Memories**

2175 Mission College Blvd.  
Santa Clara, CA 95050  
Phone (408) 970-9700  
Telex (910) 338-2374  
Telex (910) 338-2376  
Fax (408) 988-4254

## **France**

### **Monolithic Memories France S.A.R.L.**

Silic 463  
F 94613 Rungis Cedex  
France  
Phone 1-6874500  
Telex 202146  
Fax 1-6876825

## **Japan**

### **Monolithic Memories Japan KK**

5-17-9 Shinjuku  
Shinjuku  
Tokyo 160  
Japan  
Phone 3-207-3131  
Telex 232-3390 MMIKKJ  
Fax 3-207-3139

## **United Kingdom**

### **Monolithic Memories, Ltd.**

Monolithic House  
1 Queens Road  
Farnborough, Hants  
England GU146DJ  
Phone 9-011-44-252-517431  
Telex 858051 MONO UKG  
Fax (0252) 43724

## **Germany**

### **Monolithic Memories, GmbH**

Mauerkircherstr 4  
D 8000 Munich 80  
West Germany  
Phone 89-984961  
Telex 524385  
Fax 89-983162

Monolithic Memories reserves the right to make changes in order to improve circuitry and supply the best product possible.

Monolithic Memories cannot assume responsibility for the use of any circuitry described other than circuitry entirely embodied in their product. No other circuit patent licenses are implied.

Printed in U.S.A.

---